



IDS 314104 10/723 547 1/2

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	A Vertical Replacement-Gate Junction Field-Effect Transistor				
Application Number:	10/723547 				
Confirmation Number:	9745				
First Named Applicant:	Samir Chaudhry				
Attorney Docket Number:	075903-285				
Art Unit:	2811				
Search string:	(5367184 or 5599724 or 5414289 or 5576238 or 5668391 or 5744846 or 6297531 or 4366495 or 4455565 or 4587713 or 4683643 or 4786953 or 4837606 or 5342797 or 6027975 or 6072216 or 6133099 or 6197641 or 5866925 or 5889298).pn.				
US Patent Documents					
Note: Applicant is not required to submit a paper copy of cited US Patent Documents					
init	Cite.No.	Patent No.	Date	Patentee	Kind
M1	1	5367184	1994-11-22	Chantre	
✓	2	5599724	1997-02-04	Yoshida	
	3	5414289	1995-05-09	Fitch, et al	
	4	5576238	1996-11-19	Fu	
	5	5668391	1997-09-16	Kim, et al	
	6	5744846	1998-04-28	Batra, et al	
	7	6297531	2001-10-02	Armacost, et al	
	8	4366495	1982-12-28	Goodman, et al	
	9	4455565	1984-06-19	Goodman, et al	
	10	4587713	1986-05-13	Goodman, et al	
	11	4683643	1987-08-04	Nakajima, et al	
	12	4786953	1988-11-22	Morie, et al	
	13	4837606	1989-06-06	Goodman, et al	
✓	14	5342797	1994-08-30	Sapp, et al	
M1	15	6027975	2000-02-22	Hergenrother, et al	

APP_ID=10723547

Michael Trish 9/28/04

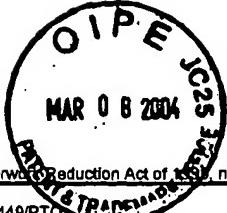
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met	16	6072216	2000-06-06	Williams, et al
↑	17	6133099	2000-10-17	Sawada
	18	6197641	2001-03-06	Hergenrother, et al
↓	19	5866925	1999-02-02	Zolper, et al
met	20	5889298	1999-03-30	Plumton, et al

Signature

Examiner Name	Date
Michael Train	9/28/04



IDS 3/8/04

PTO/SB/08B (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet

1

of

1

Complete if Known

Application Number	10/723,547
Filing Date	11/26/2003
First Named Inventor	Samir Chaudhry
Art Unit	2811 2822
Examiner Name	Unassigned

Attorney Docket Number Chaudhry 26-19-9-13-6/075903-285

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MT	1	DUDEK, ET AL, "Lithography-Independent Nanometer Silicon MOSFET's on Insulator", IEEE Transactions on Electron Devices, Vol. 43, No. 10, October 1996, pp. 1626-1631.	
MT	2	RISCH, ET AL, "Vertical MOS Transistors with 70 nm Channel Length", IEEE Transactions on Electron Devices, Vol. 43, No. 9, September 1996, pp. 1495-1498.	
MT	3	TAKATO, ET AL, "Impact of Surrounding Gate Transistor (SGT) for Ultra-High-Density LSI's", IEEE Transactions on Electron Devices, Vol. 38, No. 3, March 1991, pp. 573-577.	
MT	4	TAKATO, ET AL, "High Performance CMOS Surrounding Gate Transistor (SGT) for Ultra High Density LSIs", IEDM 1988, pp. 222-225.	
MT	5	HERGENROTHER, ET AL, "The Vertical Replacement-Gate (VRG) MOSFET: A 50-nm Vertical MOSFET with Lithography-Independent Gate Length", Technical Digest of IEDM, 1999, pp. 75-78.	
MT	6	OH, ET AL, "50 nm Vertical Replacement-Gate (VRG) pMOSFETs", IEEE 2000, 4 pages	
MT	7	HERGENROTHER, ET AL, "The Vertical Replacement-Gate (VRG) MOSFET: A High Performance Vertical MOSFET with Lithography-Independent Critical Dimensions", no publication information apparent from document, 1 pages .	
MT	8	MONROE, ET AL, "The Vertical Replacement-Gate (VRG) Process for Scalable, General-purpose Complementary Logic", Paper 7.5, pp. 1-7, date and publication information unknown.	

Examiner Signature	<i>Michael Trinh</i>	Date Considered	<i>9/28/04</i>
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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